TECHNICAL DATA
DATA SHEET 4009, REV. A

HERMETIC SCHOTTKY RECTIFIER
Very Low Forward Voltage Drop

Features:

- **Soft Reverse Recovery at Low and High Temperature**
- **Very Low Forward Voltage Drop**
- **Low Power Loss, High Efficiency**
- **High Surge Capacity**
- **Guard Ring for Enhanced Durability and Long Term Reliability**
- **Guaranteed Reverse Avalanche Characteristics**

Maximum Ratings

Characteristics	Symbol	Condition	Max.	Units
Peak Inverse Voltage	V_{RWM}	-	45	V
Max. Average Forward Current	$I_{F(AV)}$	50% duty cycle, rectangular wave form (Single)	15	A
Max. Average Forward Current	$I_{F(AV)}$	50% duty cycle, rectangular wave form (Common Cathode)	30	A
Max. Peak One Cycle Non-Repetitive Surge Current	I_{FSM}	8.3 ms, half Sine wave (per leg)	200	A
Non-Repetitive Avalanche Energy	E_{AS}	$T_J = 25\ °C$, $I_{AS} = 3.0\ A$, $L = 4.4\ mH$ (per leg)	20	mJ
Repetitive Avalanche Current	I_{AR}	I_{AS} decay linearly to 0 in 1 μs f limited by T_J max $V_A = 1.5 V_R$	3.0	A
Maximum Thermal Resistance	$R_{\theta JC}$	(Single) (Common Cathode)	1.21 0.61	°C/W
Max. Junction Temperature	T_J	-	-65 to +175	°C
Max. Storage Temperature	T_{stg}	-	-65 to +175	°C

Electrical Characteristics

Characteristics	Symbol	Condition	Max.	Units
Max. Forward Voltage Drop (per leg)	V_{F1}	@ 15A, Pulse, $T_J = 25\ °C$	0.73	V
	V_{F2}	@ 15A, Pulse, $T_J = 125\ °C$	0.66	V
Max. Reverse Current	I_{R1}	@$V_R = 45V$, Pulse, $T_J = 25\ °C$	2.0	mA
(per leg)	I_{R2}	@$V_R = 45V$, Pulse, $T_J = 125\ °C$	15	mA
Max. Junction Capacitance (per leg)	C_T	@$V_R = 5V$, $T_C = 25\ °C$ $f_{SIG} = 1MHz$, $V_{SIG} = 50mV$ (p-p)	800	pF

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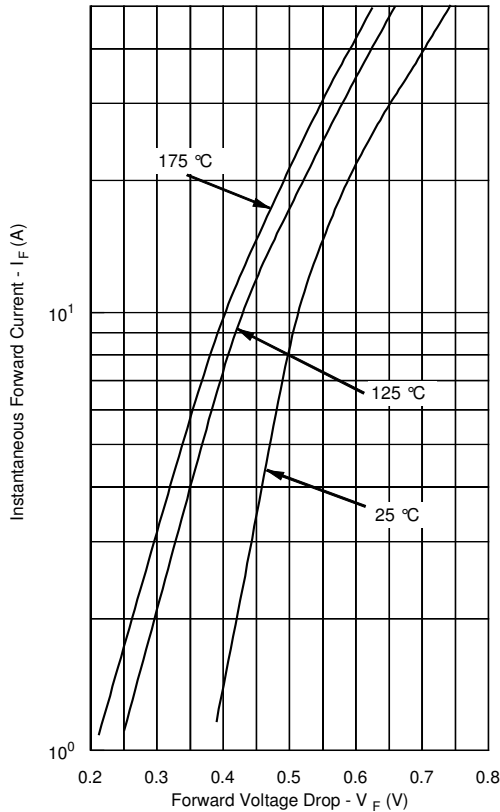## Mechanical Dimensions: in Inches / mm   **LCC-5**

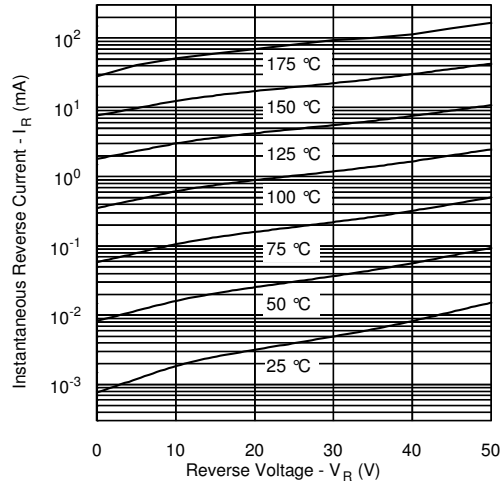**SINGLE**

1   2   3
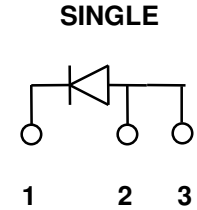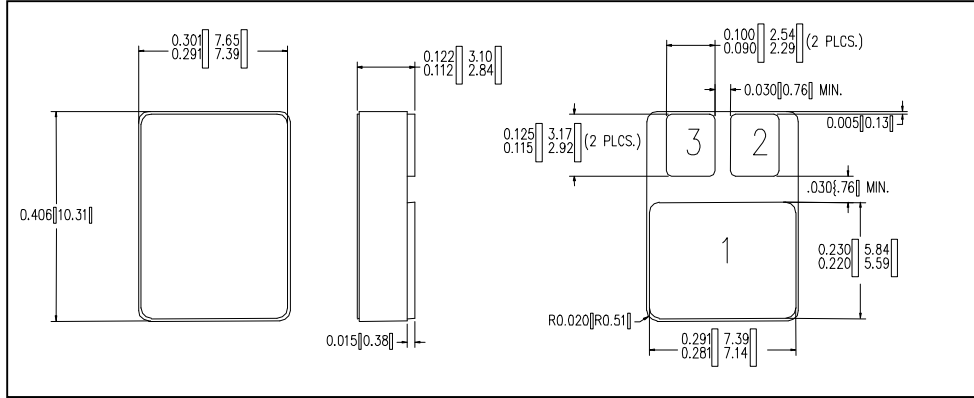
PINOUT TABLE

DEVICE TYPE	PIN 1	PIN 2	PIN 3
SINGLE RECTIFIER	CATHODE	ANODE	ANODE

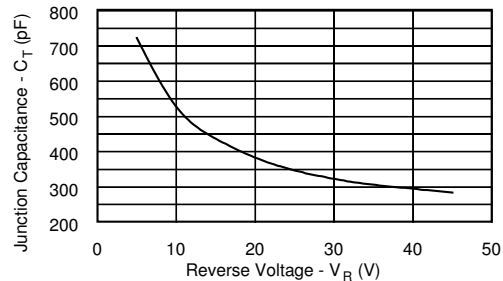**Note:** The V_f curves shown are for the SD125SB45 unpackaged die only.

Typical Forward Characteristics

Typical Reverse Characteristics

Typical Junction Capacitance

TECHNICAL DATA

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